



#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### Features

- Low On-Resistance: R<sub>DS(ON)</sub>
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)

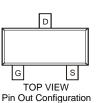
## **Mechanical Data**

- Case: SOT-23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

SOT-23



TOP VIEW



## **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Charae	cteristic	Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Drain-Gate Voltage R <sub>GS</sub> ≤ 1.0MΩ	1	V <sub>DGR</sub>	60	V
Gate-Source Voltage	Continuous Pulsed	V <sub>GSS</sub>	±20 ±40	V
Drain Current	Continuous	I <sub>D</sub>	240	mA

#### **Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	PD	300	mW
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	417	°C/W
Operating and Storage Temperature Range	Tj, T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symphol	Mim	Turn	Max	الم ال	Test Condition
		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					-		1
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	60	70	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ $T_{C} = 25^{\circ}C$	Inco			1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Ŭ	@ T <sub>C</sub> = 125°C	IDSS			500	μ. ι	$v_{\rm DS} = 00v$ , $v_{\rm GS} = 0v$
Gate-Body Leakage		I <sub>GSS</sub>			±10	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage		V <sub>GS(th)</sub>	1.0		2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	@ T <sub>J</sub> = 25°C	R <sub>DS (ON)</sub>	_	1.6	3	Ω	$V_{GS} = 10V, I_{D} = 250mA$
		TOS (ON)		2.0	4		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA
On-State Drain Current		I <sub>D(ON)</sub>	0.8	1.0	_	Α	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance		<b>g</b> fs	80	_	_	mS	V <sub>DS</sub> =10V, I <sub>D</sub> = 0.2A
DYNAMIC CHARACTERISTICS							
Input Capacitance		Ciss		22	50	pF	
Output Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C <sub>rss</sub>	_	2.0	5.0	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t <sub>D(ON)</sub>	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t <sub>D(OFF)</sub>		11	20	ns	$R_L = 150\Omega$ , $V_{GEN} = 10V$ , $R_{GEN} = 25\Omega$

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

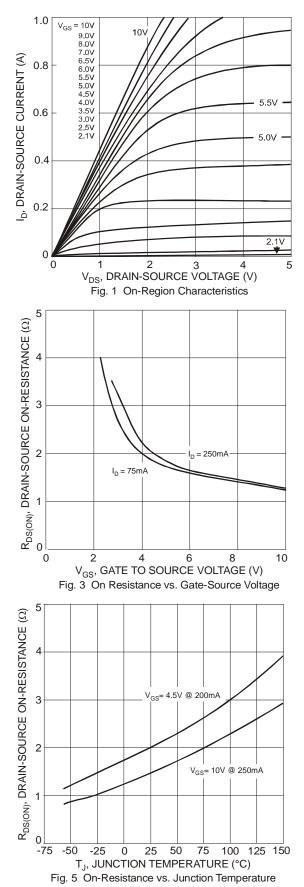
2. No purposefully added lead. Halogen and Antimony Free.

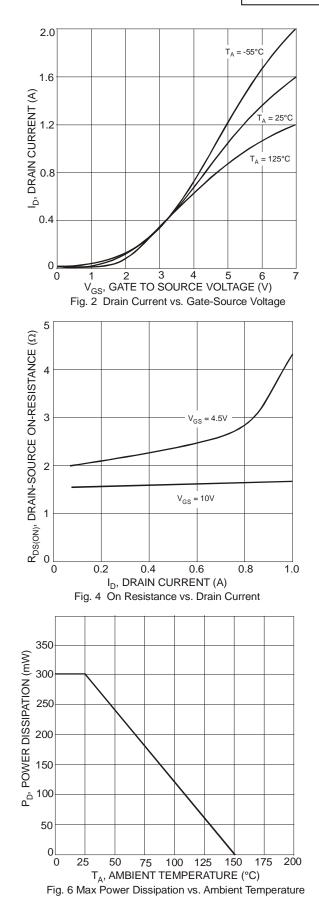
3. Short duration pulse test used to minimize self-heating effect.

 Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb203 Fire Retardants.



# 2N7002E





NEW PRODUCT

2N7002E Document number: DS30376 Rev. 7 - 2

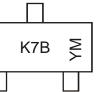


## Ordering Information (Note 5)

Part Number	Case	Packaging
2N7002E-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**

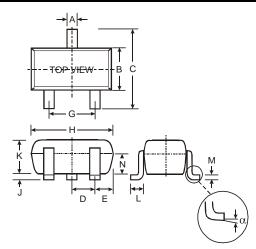


K7B = Product Type Marking Code YM = Date Code Marking Y = Year ex: P = 2003 M = Month ex: 9 = September

Date	Code	Kev

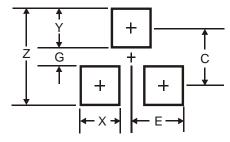
Year	2003	2004	20	05	2006	2007	2008	2009	) 2	010	2011	2012
Code	Р	R	S	S	Т	U	V	W		Х	Y	Z
Month	Jan	Feb	Mar	Ар	r May	Jun	Jul	Aug	Sep	Oc	t Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

## **Package Outline Dimensions**



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	<b>D</b> 0.89 1.03				
E	0.60				
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	1.10				
L	L 0.45 0.61				
М	M 0.085 0.18				
Ν	N				
α	0°	8°			
All Dir	All Dimensions in mm				

## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Y	1.4
С	2.0
E	0.9

#### IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

#### LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.